



Silicon Photonics

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Agenda **Motivation** History & Progress Intel's Research Program **Building Block Results** -Modulator, detector, hybrid laser Integrated 200Gb/s Test chip Future work and Summary



Moving to Interconnects



Tera-leap to Parallelism:



Future Physical I/O for Tera-scale Servers



Integrated Tb/s Optical Chip?





A future integrated terabit per second optical link on a single chip

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Photonics Evolution



Silicon as an Optical Material



- ✓Transparent > ~1.1 μm
- ✓ High index
- CMOS Compatible
- ✓Low cost material

8 Low light emission efficiency
8 No electro-optical effect
8 No detection in 1.3-1.6 μm

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Silicon traditionally NOT optical material of choice



Si Photonics Recent Progress

*This is not exhaustive

Pioneering work by Dr. Richard Soref	Integrated APD+TIA UT Inverted Taper NTT, Cornel	Raman λ Conv. UCLA Modeled GHz PIN Modulator Surrey, Naples DGADC Surrey PBG WG <25dB/cm IBM	Polarization Indep. Rings Surrey Raman Laser UCLA >GHz MOS Modulator Intel 30GHz Si-Ge Photodetector IBM PBG WG <7dB/cm IBM, FESTA, NTT	QCSE in Si Stanford Stim-Emission Brown CW Raman Laser Intel 10Gb/s Modulator Intel, Luxtera 1.5Gb/s Ring Mod. Cornell 39GHz Si-Ge Photodetector Univ. Stuttgart PBG WG <3db/cm NTT	Hybrid Silicon Laser Intel - UCSB Broadband Amplification Cornell E-O Effect Strained-Si 4 DTU OGb/s SiGe PIN Commercial Quality Intel	40Gb/s Raman Amp & λ Conv. Ring Laser Intel OGb/s Modulator Intel 40Gb/s SiGe Wave Guide PIN Intel
	2002	2003	2004	2005	2006	2007
		Devic s	ce perform ignificant a	ance making advances	10	(intel Leap ahead"

Intel's Silicon Photonics Research



First: Innovate to prove silicon is a viable optical material

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Intel Leap ahead"

Intel's Silicon Photonics Research

Innovating with low-cost silicon to create new optical devices



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Integration Vision





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Future work & Summary



Modulation

Direct or External modulation External used for 10G at ~12km+



Intel's Second Generation: Silicon Modulator



SEM picture of p-n phase shifter

-Based on traveling wave design -Optimized optical & electrical RF



40 Gbps Data Transmission



- Optical 3 dB roll off ~30 GHz (parasitic effect included)
- 6 dB electrical roll-off ~ 40 GHz (no parasitic effect included)
- Measured phase efficiency = 3.3 V-cm



Photodetection

10-1 10 Silicon does not absorb IR well Ge Using SiGe to extend to 1.3µm+ 100 Absorption coefficient [cm⁻¹] 10 Must overcome lattice mismatch Penetration depth [µm] 103 Bulk Films of Si and Ge Strained Si_{1-x}Ge_x on Si Relaxed Si_{1-x}Ge_x on Si D 53 10² 102 Si 0 0 0 0 00 0 0 0 00 0 0 0 010 \bigcirc \bigcirc \bigcirc \bigcirc \bigcirc \bigcirc \bigcirc \checkmark $a_{Ge} \sim .565 nm$ 0.4 0,6 0,8 1,0 1,2 1,4 1,6 1.8 wavelength (µm) misfit a_{si} ~ .543 nm dislocation

Misfit dislocations typically create threading dislocations which degrade device performance - *dark current* (I_{dk}) goes up.

Must simultaneously achieve required speed, responsivity, & dark current.



Waveguide Photodetector Design







SiGe WG PIN - High Speed Performance



31 GHz Optical Bandwidth



40 Gb/s Eye Diagram

95% Quantum Efficiency Operating at $\lambda \sim 1.56$ um < 200nA of dark current



Hybrid Silicon Laser Collaboration with UCSB

The Indium Phosphide emits the light into the silicon waveguide



The silicon acts as laser cavity: Silicon waveguide routes the light Laser performance determined by Silicon waveguide i.e WDM performance determined by etch silicon gratings

> No alignment needed 10's if not 100's of lasers with ONE bond Combines best of both materials



Hybrid Laser Structure





SEM (Scanning Electron Microscope) Photograph



Single Wavelength Hybrid Laser



Single Wavelength Results



- 8 mW output power at room temperature
- Single wavelength with 50 dB side mode suppression ratio
- 3.6 MHz line width (de-convolved from measurement)



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Integrated SiP Test chip

Learning Vehicle: target >100Gb/s



• Learning vehicle for:

- Process integration
- Electrical and high speed packaging
- Performance, die variation, uniformity







Integrated TX: Results





- All 8 channels yielded open 25 Gbps optical eyes close to expectation.
- Aggregate data rate of 200 Gbps
- Good step toward Tb/s ...





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Future work & Summary





A future integrated terabit per second optical link on a single chip



Integrating into a Tera-scale System

This transmitter would be combined with a receiver

Which could then be built into an integrated, silicon photonic chip!!

Тх

Rx



Integrating into a Tera-scale System



This integrated silicon photonic chip could then be integrated into computer boards

And this board could be integrated into a Tera-sca system



Summary

Future multi-core processors will continue to drive I/O bandwidth needs to ~Tb/s data rates in near future pushing need for optical interconnects

Cost will be primary driver for enabling optical links in and around the PC and Server

Silicon Photonics device performance advancing at a rapid rate. Need to continue pushing higher levels of integration (ie 200G, 400G etc)

Next phase of challenges will be with integration combined with low cost packaging

Overall solution must focus on power efficiency, integration and cost tradeoffs



Silicon Photonics' Future



Electronics: Economics of Moore's Law

SCALING + WAFER SIZE + HIGH VOLUME = LOWER COST



Integration & increased functionality

Leap ahead"

The Opportunity of Silicon Photonics

Enormous (\$ billions) CMOS infrastructure, process learning, and capacity

Draft continued investment in Moore's law
 Potential to integrate multiple optical devices
 Micromachining could provide smart packaging
 Potential to converge computing & communications



To benefit from this optical wafers must run alongside existing product.



Guiding Light with Si Waveguides





Proven area for silicon High index = small structures – Strip and Photonic crystals for further scaling Splitters, couplers, gratings, AWGs, MMIs have all been demonstrated

> Continue to reduce size while maintaining performance

